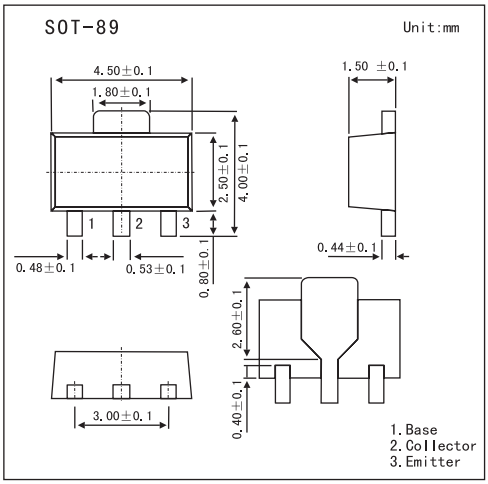
Silicon PNP Epitaxial

2SB1025



■ Features

- Low frequency power amplifier

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-120	V
Collector to emitter voltage	V_{CEO}	-80	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-1	A
peak collector current	I_{CP} *1	-2	A
Collector power dissipation	P_C *2	1	W
Junction temperature	Tj	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

*1. PW ⩽ 10 ms; d ⩽ 0.02.

*2. Value on the alumina ceramic board (12.5 □ 20 □ 0.7 mm)

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	I_C = -10 μA, I_E = 0	-120			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	I_C = -1 mA, R_{BE} = ∞	-80			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	I_E = -10 μA, I_C = 0	-5			V
Collector cutoff current	I_{CBO}	V_{CB} = -100V, I_E = 0			-10	μA
DC current transfer ratio	h_{FE}	V_{CE} = -5 V,I_C = -150 mA	60		320	
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = -500 mA,I_B = -50 mA			-1	V
Base to emitter voltage	V_{BE}	V_{CE} = -5 V,I_B = -150 mA			-0.9	V
Gain bandwidth product	f_T	V_{CE} = -5 V,I_C = -150 mA		140		MHz
Collector output capacitance	C_{ob}	V_{CB} = -10 V, I_E = 0,f = 1 MHz		20		pF

■ h_{FE} Classification

Marking	DH	DJ	DK
hFE	60～120	100～200	160～320